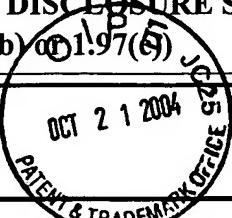


**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))**

Docket No.
OKI.206D3

In Re Application Of: **Masahiro Yoshida et al.**



Application No.	Filing Date	Examiner	Customer No.	Group Art Unit	Confirmation No.
10/762,361	January 23, 2004	W. Lindsay, Jr.		2812	4915

**Title: METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE INCLUDING A MOSFET WITH
NITRIDE SIDEWALLS**

Address to:

**Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450**

37 CFR 1.97(b)

1. The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

- the statement specified in 37 CFR 1.97(e);

OR

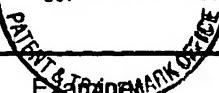
- the fee set forth in 37 CFR 1.17(p).

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

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In Re Application: **Masahiro Yoshida et al.**

OCT 21 2004



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10/762,361	January 23, 2004	W. Lindsay, Jr.		2812	4915

Title: **METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE INCLUDING A MOSFET NITRIDE SIDEWALLS**

Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- A check in the amount of _____ is attached.
- The Director is hereby authorized to charge and credit Deposit Account No. 50-0238 as described below.
- Charge the amount of _____
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WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.

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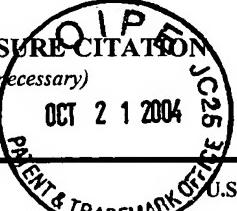
ANDREW J. TELESZ, JR.

REG. NO. 33,581

Dated: October 21, 2004

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TEL. NO. (703) 715-0870

CC:

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i> 				Docket Number (Optional) OKI206D3		Application Number 10/762,361		
				Applicant(s) Masahiro Yoshida et al.				
				Filing Date January 23, 2004		Group Art Unit 2812		
				U.S. PATENT DOCUMENTS				
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
U.S. PATENT APPLICATION PUBLICATIONS								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
A	Focused Technology Report; Report Number: FTR 9912-008; Comparative Analysis of Advanced Sub-Micron Transistor Technology; By Integrated Circuit Engineering Corporation; 1999							
EXAMINER				DATE CONSIDERED				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								